

FEATURES

- n **HIGH POWER**
P1dB=33.0dBm at 9.5GHz to 12.0GHz
- n **HIGH GAIN**
G1dB=25.0dB at 9.5GHz to 12.0GHz
- n **BROAD BAND INTERNALLY MATCHED**
- n **HERMETICALLY SEALED PACKAGE**

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain Supply Voltage	VDD	V	15
Gate Supply Voltage	VGG	V	-10
Input Power	Pin	dBm	15
Flange Temperature	Tf	°C	-30 ~ +80
Storage Temperature	Tstg	°C	-65 ~ +175

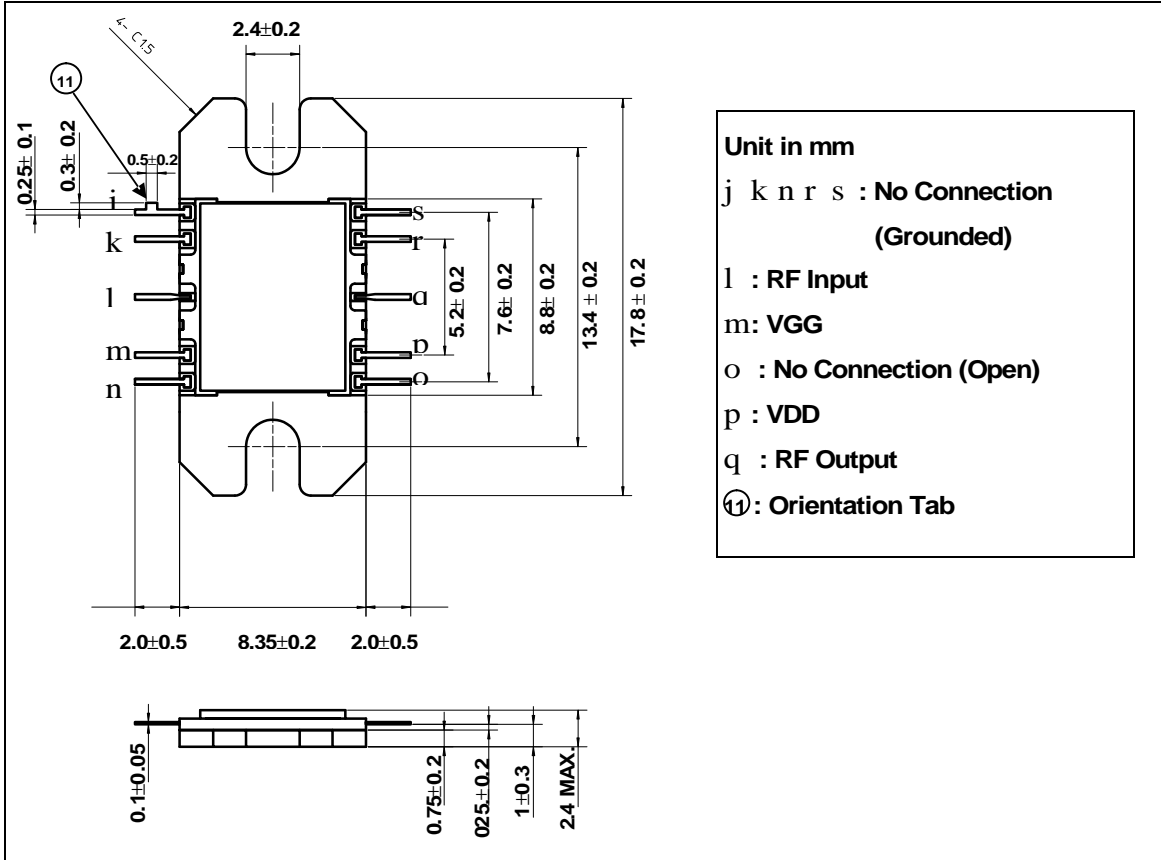
RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDD= 10V VGG= -5V f = 9.5 – 12.0GHz	dBm	31.0	33.0	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	21.0	25.0	—
Gain Flatness	ΔG		dB	—	—	±2.5
Drain Current	IDD		A	—	1.4	1.8
Power Added Efficiency	ηadd		%	—	14	—
3 rd Order Intermodulation Distortion	IM3	2 tone @ Po=19dBm(S.C.L.)	dBc	-42	-45	—

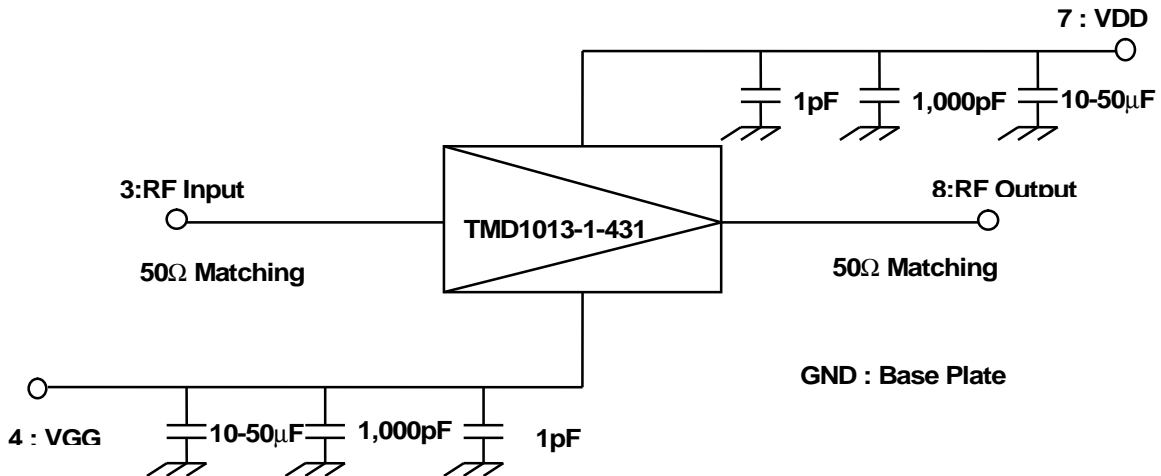
The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of TOSHIBA or others.

The information contained herein is subject to change without prior notice. It is therefore advisable to contact TOSHIBA before proceeding with design of equipment incorporating this product.

PACKAGE OUTLINE (2-9E1D)



RECOMMENDED BIAS CONFIGURATION



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C . Flanges of devices should be attached using screws and washers. Recommended torque is $0.18\text{-}0.20$ N-m.